

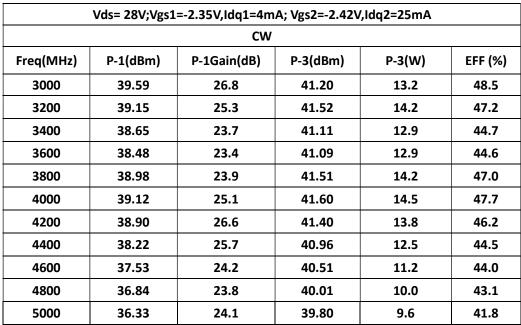
# Innogration (Suzhou) Co., Ltd.

## 3.0-5.0GHz, 10W, 28V High Gain GaN Fully matched PA Module

### **Description**

The G2MAH3050-10C9 is a 10-watt **,2 stage/high gain** integrated Power Amplifier Module, designed for broad band applications, with frequencies from 3 to 5GHz. The module is 50  $\Omega$  input/output matched and requires minimal external components. It can work at higher voltage like 32V with increased power capability

The module implements wideband power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.





#### **Product Features**

• Operating Frequency Range: 3-5GHz

• Operating Drain Voltage: +28 V

• 50  $\Omega$  Input/Output

• Psat≥40 dBm

• Small signal gain:>25dB, Power gain:>22dB

• Minimum efficiency:>40%

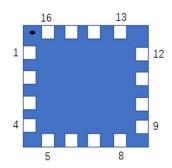
• 12x10 mm Surface Mount Package

• Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

#### **Applications**

- Ultra Broadband Amplifiers
- Fiber Drivers
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

## Pin Configuration and Description (Top view)



Pin No.	Symbol	Description
1	RF IN	RF Input
9	RF OUT	RF Output
16	Vgs1	Gate bias for 1 <sup>st</sup> stage
15	Vdd1	Drain bias for 1 <sup>st</sup> stage
6	Vgs2	Gate bias for 2nd stage
7	Vdd2	Drain bias for 2nd stage
Others	NC	No connection
		DC/RF Ground. Proposed to be soldered to heatsink plane directly for the best CW thermal
Package Base	GND	and RF performance. Soldered through high density vias or copper coin also allowed ,but
		will result in excessive junction temperatures and different RF performance

#### **Table 1. Maximum Ratings**

Symbol	Value	Unit
$V_{\scriptscriptstyle DSS}$	150	Vdc
$V_{\sf GS}$	-10 to +2	Vdc
$V_{DD}$	+36	Vdc
Tstg	-65 to +150	°C
Tc	+150	°C
T,	+225	°C
	V <sub>DSS</sub> V <sub>GS</sub> V <sub>DD</sub> Tstg Tc	V <sub>DSS</sub> 150 V <sub>SS</sub> -10 to +2 V <sub>DD</sub> +36 Tstg -65 to +150 T <sub>C</sub> +150

#### **Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Do 10	G	0C/M
T <sub>C</sub> = 85°C, T <sub>J</sub> =175°C, DC test	Rejc	6	°C/W

### **Table 3. Electrical Characteristics**

Parameter	Condition	Min	Тур	Max	Unit
Frequency Range		3000		5000	MHz
Power Gain @ Psat		23			dB
P <sub>SAT</sub>	Pulse		40		dBm
Drain Efficiency @ P <sub>SAT</sub>		40			%
Unless otherwise noted: TA = 25°C, Vpp =28 V. Pulse Width=50 us. Duty cycle=20%					

Load Mismatch of per Section (On Test Fixture, 50 ohm system): V<sub>DD</sub> =28 V, I<sub>DQ</sub> =25 mA, f = 3.5 GHz

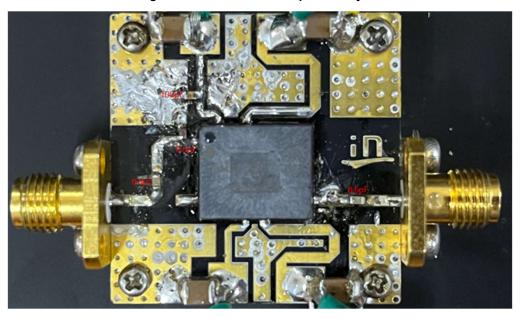
VSWR 10:1 at Psat pulse CW Output Power	No Device Degradation
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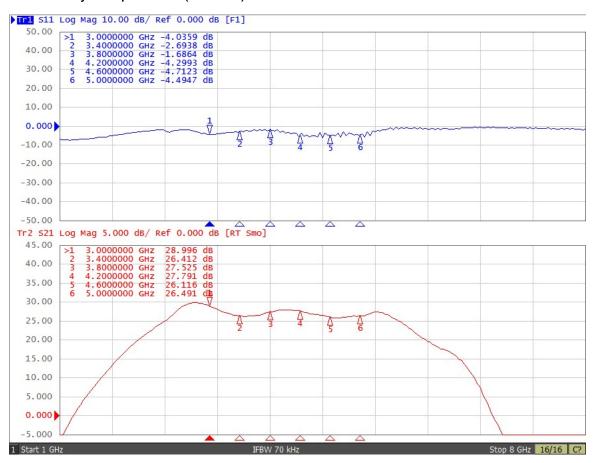
### **Reference Circuit of Test Fixture Assembly Diagram**

Figure 1. Test Circuit Component Layout



#### TYPICAL CHARACTERISTICS

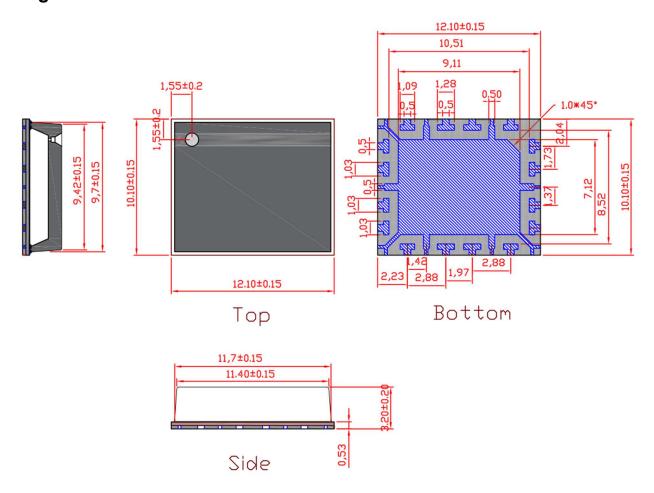
Figure 2. Network analyzer output S11/S21 (Pin=0dBm)





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## Package Dimensions (Unit:mm)



#### **Revision history**

Table 6. Document revision history

Date	Revision	Datasheet Status
2023/2/14	Rev 1.0	Preliminary Datasheet
2023/7/2	Rev 1.1	Modify the gain flatness

Application data based on HJ-23-02

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